

In The Claims:

1-30 cancelled.

31. (Original) A method of underfilling a gap between a multi-sided semiconductor device and a substrate to encapsulate a plurality of electrical connections formed therebetween, comprising:

forming a channel between said device and said substrate;

leaving said channel open to at least one side of said device to permit access to said device; and

dispensing an under-fill material adjacent said at least one side of said device through said channel.

32. (Original) The method of claim 31 wherein said channel permits the removal of residual flux.